



DACO SEMICONDUCTOR CO., LTD.

MBRA80030CTL

## LOW VF SCHOTTKY DIODE MODULE TYPE 800A

### Features

High Surge Capability

800Amp Rectifier  
30 Volts

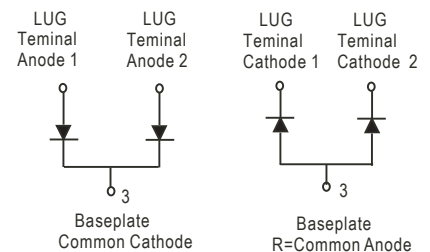
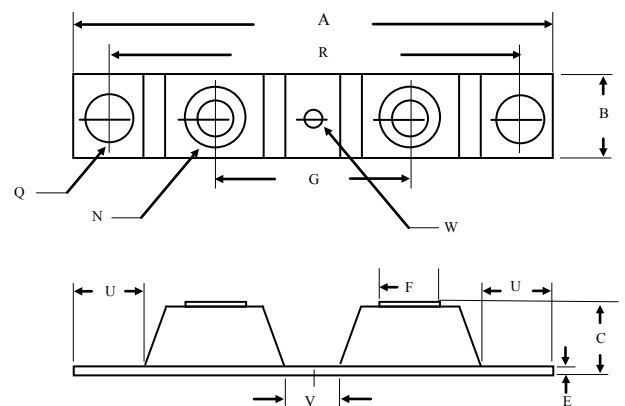
### Maximum Ratings

Operating Temperature:  $-40^{\circ}\text{C}$  to  $+100^{\circ}\text{C}$

Storage Temperature:  $-40^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBRA80030CTL	30V	21V	30V

### HEAVY TWIN TOWER



### Electrical Characteristics @ $25^{\circ}\text{C}$ Unless Otherwise Specified

Average Forward Current (Per pkg)	$I_{F(AV)}$	800A	$TC=100^{\circ}\text{C}$
Peak Forward Surge Current (Per leg)	$I_{FSM}$	6000A	8.3ms, half sine
Maximum Instantaneous Forward Voltage (Per leg)	$V_F$	0.58V	$I_{FM}=400A; T_J=25^{\circ}\text{C}$
Maximum Instantaneous Reverse Current At Rated DC Blocking Voltage (Per leg)	$I_R$	3.0 mA 300mA	$T_J = 25^{\circ}\text{C}$ $T_J = 100^{\circ}\text{C}$
Maximum Thermal Resistance Junction To Case (Per leg)	$R_{\theta jc}$	$0.25^{\circ}\text{C/W}$	

NOTE :

(1) Pulse Test: Pulse Width 300  $\mu$  sec. Duty Cycle  $< 2\%$

DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	-----	3.64	-----	92.3
B	1.06	1.067	26.9	27.1
C	-----	0.740	-----	18.8
E	0.134	0.14	3.4	3.55
F	0.520	0.527	13.2	13.4
G	1.49	BSC	38.0	BSC
N	1/4-20 UNC FULL			
Q	0.275	0.290	6.99	7.37
R	3.150	BSC	80.01	BSC
U	0.512	-----	13.0	-----
V	0.449	0.472	11.4	12.0
W	0.180	0.195	4.57	4.95



Figure .1-Typical Forward Characteristics

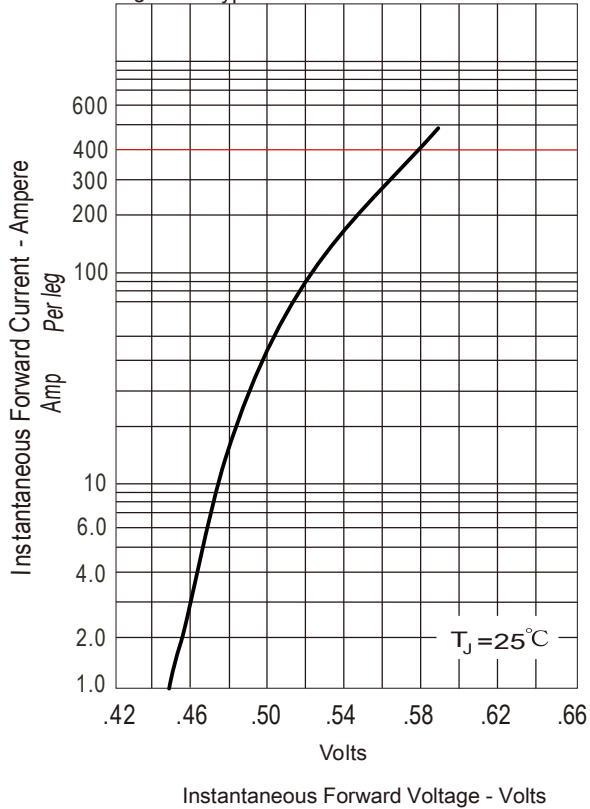


Figure .2- Forward Derating Curve

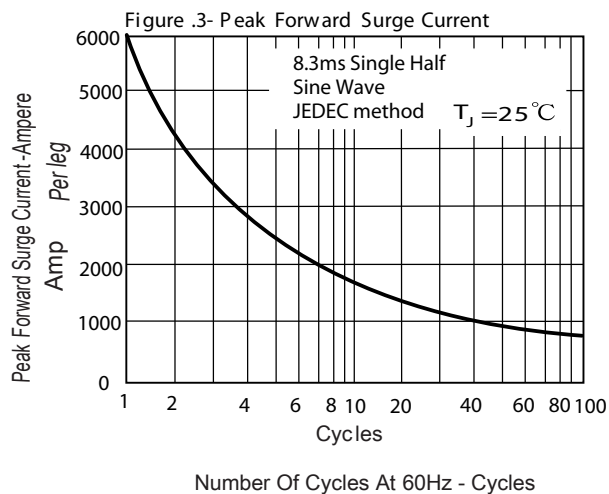
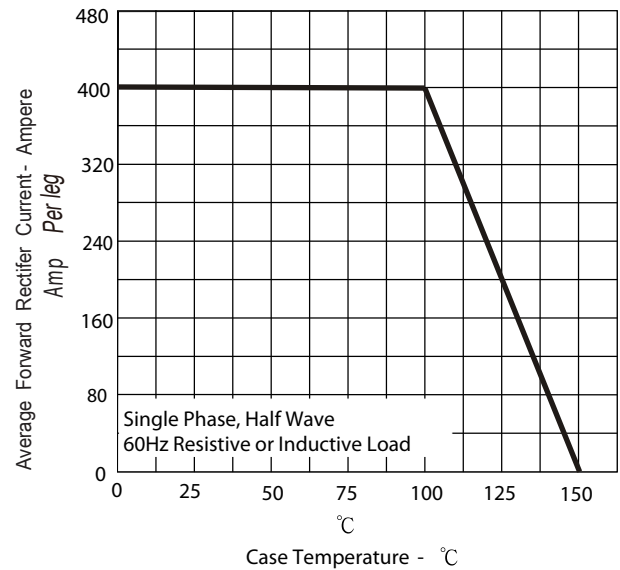


Figure .4-Typical Reverse Characteristics

